

WHAT IS CLAIMED IS:

1. A semiconductor integrated circuit device, comprising a digital circuit part and an analog circuit part that are disposed on a surface of one semiconductor substrate,
wherein a dummy layer part made of polysilicon that is the same as polysilicon composing a gate of a transistor is disposed between the digital circuit part and the analog circuit part.
2. The semiconductor integrated circuit device according to claim 1, wherein a dummy region further is provided between the digital circuit part and the analog circuit part, and a power-supply potential is applied to the dummy region.
3. The semiconductor integrated circuit device according to claim 1, wherein the digital circuit part is a circuit for driving a sensor array, and the analog circuit part is a circuit for analog processing an image detecting signal that is output from the sensor array.
4. The semiconductor integrated circuit device according to claim 3, wherein the sensor array is a CCD area sensor, a CCD linear sensor or a CMOS sensor.
5. A camera, comprising:
an imaging element; and
a semiconductor integrated circuit device comprising a digital circuit part for driving the imaging element and an analog circuit part for analog processing an image detecting signal output from the imaging element,
wherein the semiconductor integrated circuit device has a structure in which a dummy layer part made of polysilicon that is the same as polysilicon composing a gate of a transistor is disposed between the digital circuit part and the analog circuit part.